[Contribution from the Gates and Crellin Laboratories of Chemistry, California Institute of Technology, No. 845]

An Electron Diffraction Investigation of the Molecular Structures of Silicon Tetrabromide, Tribromosilane, and Dibromodifluorosilane

By Ralph Spitzer, W. J. Howell, Jr., and Verner Schomaker

Introduction.-The bond lengths in the halides of the fourth, fifth, and sixth group elements are in general considerably shorter than the sums of the corresponding Pauling-Huggins covalent radii.¹ This discrepancy appears to be partially resolved by the introduction of a correction for the partial ionic character of the bonds²; however, large disparities remain for the second row fluorides, while for the heavier halides the agreement is not precise. For the bromosilanes considered in this paper, the Si-Br distances are found to be 2.16 ± 0.03 Å., 0.06 Å. shorter than the distance calculated by Schomaker and Stevenson.² The bond-angle values reported here are all approximately tetrahedral with the exception of that for F-Si-F in SiF₂Br₂, which seems to be decidedly less than tetrahedral. This value may be in error, however, as noted below.

We have found approximate values for the relative amplitudes of vibration $\delta l_{ij}^2 - \delta l_{\text{SiBr}^2}$ in silicon tetrabromide and tribromosilane which should be helpful in connection with the spectroscopic data for the consideration of the normal modes of vibration and vibrational potential functions of these molecules.

Experimental.—The apparatus and technique employed have been described by Brockway.³ The wave length of the electrons was determined from transmission photographs of gold foil ($a_0 = 4.070$ Å.), and was about 0.06 Å.

We are indebted to Professor W. C. Schumb of the Massachusetts Institute of Technology for supplying us with the samples used.

Interpretation.—In interpreting the photographs the correlation method was used in conjunction with the radial distribution method described by Schomaker.⁴ The simplified theoretical intensity curves for the various models were calculated according to the formula

$$I(\mathbf{s}) = \frac{1}{(Z_{\rm Si} - f_{\rm Bi})(Z_{\rm Br} - f_{\rm Br})} \sum_{ij}' (Z_i - f_i)(Z_j - f_j)e^{-a_ijs^2} \frac{\sin l_{ij}s}{l_{ij}s} \quad (1)$$

in which account is taken of the variation with s of the relative scattering powers of the various atoms and of the effect of the harmonic vibrations of the molecule. Z_i is the atomic number of atom *i*; f_i , the atom form factor⁵; l_{ij} , the interatomic distance; a_{ii} , one-half the mean square amplitude of vibration of atom i against atom j; and $s = 4\pi/\lambda \sin \varphi/2$ where λ is the electron wave length and φ is the scattering angle. Since the calculation of a_{ii} from spectroscopic data is not feasible at present for polyatomic molecules having large moments of inertia, an attempt was made to determine these temperature-factor constants by including them as parameters in the correlation treatment. a_{Si-Br} was arbitrarily set equal to zero, so that the quantities actually determined are $a_{ij} - a_{Si-Br}$; for brevity we call these quantities a_{ij} . The values reported refer to the effective temperature of the scattering gas, about 25° for SiHBr₃ and SiF₂Cl₂, and about 100° for SiBr₄.

The radial distribution formula used was

 $D(l) = \sum_{n} C_n \frac{\sin s_n l}{s_n l}$

with

and

$$e^{-as^2\max} = 0.1$$

 $C_n = I_n s_n e^{-as^2 n}$

where I_n is a relative intensity, estimated for the various peaks so as to show no average dependence on *s*, and s_{\max} is for the last observable feature on the photograph.

Silicon Tetrabromide.—The two parameters to be determined were l, the Si-Br distance, and a, the temperature-factor constant for Br-Br vibration. The molecule was assumed to have the symmetry of a regular tetrahedron.

The photographs showed a rather heavy background which tended to make the measurements less precise than usual. The difficulty of meas-

⁽¹⁾ L. Pauling and M. L. Huggins, Z. Krist., 87, 205 (1934).

⁽²⁾ V. Schomaker and D. P. Stevenson, THIS JOURNAL, 63, 37 (1941).

⁽³⁾ L. O. Brockway, Rev. Mod. Phys., 8, 231 (1936).
(4) V. Schomaker, Thesis, California Institute of Technology.

 ⁽⁴⁾ V. Schomaker, Thesis, California Institute of Technology, 1938; American Chemical Society meeting, Baltimore, Md., April, 1939.

⁽⁵⁾ L. Pouling and J. Sherman, Z. Krist., 81, 1 (1932).

urement was enhanced by the slight, but deceptive, asymmetry of some of the peaks. In all, twenty-six features were measured and used in the radial distribution curve; of these, the first five and last six were rejected in the quantitative comparison with theoretical intensity functions since it was felt that these measurements were less reliable than the others. The observed values of sare given in Table I, together with values of I_n

			TAB	LEI		
Max,	Min.	I_n	C_n	50	Scaled.	s/so
	1	- 3	- 2	1.54		
1		2	2	2.39		
	2	- 2	- 2	3.25		
2		7	10	4.11		
	3	-10	-17	5.00	4.94	(0.988)
3		5	10	5.99	5.91	.987
	4	- 5	-10	6.78	6.75	. 996
4		4	9	7.63	7.54	.988
	5	-10	-23	8.53	8.42	. 987
5		10	24	9.45	9.42	.997
	6	- 7	-17	10.37	10.39	1.002
6		4	10	11,19	11.31	1.011
	7	- 3	- 7	12.08	11.95	0.989
7		6	14	12.71	12.89	1.014
	8	-10	-22	13.84	13.90	1.005
8		10	21	14.68	14.87	1.014
	9	- 3	- 6	15.65	15.76	1.007
9		4	7	16.49	16.41	0.995
	10	- 7	-11	17.26	17.34	1.005
10		10	15	18.23	18.35	1.007
	11	-10	-13	19.41	19.44	$(1.002)^{a}$
11		5	6	20.19	20.24	(1.002)
	12	- 1	- 1	21.05	21.05	(1.000)
12		5	5	21.60	21.70	(1.005)
	13	- 6	- 5	22.85	22.77	(0,996)
13		9	7	23.71	23.97	(1.011)
				Average	e	1.000
				Average	e deviatio	on 0.008
				$l_{\mathrm{Si-Br}}$		2.145 Å.

^a Ratios enclosed in parentheses were not used in the quantitative comparison.

and C_n used in the radial distribution function, and values of $s_{calcd.} s_0$. The curves were calculated for l_{Si-Br} equal to 2.145 Å.

The curves D, E and F (Fig. 1) correspond to a = 0, 0.001 and 0.003, respectively. None of the curves shows marked disagreement with the photographs; the best correlation would be attained with some curve between B and C. This fixes the value of a between 0.001 and 0.003. Figure 1a shows the radial distribution curve for silicon tetrabromide.

The average value for the Si-Br distance obtained from fifteen features by the correlation method was 2.145 Å. with an average deviation



Fig. 1.—Radial distribution functions: simplified theoretical intensity curves for SiBr₄.

of 0.9 per cent. This gives 3.50 Å. for the Br–Br distance. The radial distribution function (Fig. 1) gives

$$l_{\text{Si-Br}} = 2.16 \text{ Å.}, l_{\text{Br-Br}} = 3.51 \text{ Å.}$$

Since the Br-Br distance is the more reliable, we base our value of l on it. The estimated best values are

$$U_{Br-Br} = 3.51 \pm 0.03 \text{ Å}.$$

 $l_{Si-Br} = 2.15 \pm 0.02 \text{ Å}.$
 $a = 0.002$

Tribromosilane.—Thirty features were measured, of which twenty were used for the quantitative comparison with the theoretical curves. The photographs were better than those for silicon tetrabromide. The values assumed for the Br-Si-Br angle ϑ were 113° (curve A), 111° (B), 109.28′ (C), and 107° (D). The Si-Br distance was set at 2.15 Å. in the calculations. The curves in Fig. 2 are divided into three groups—curves A, B, C, D, with a = 0, A', B', C' and D' with a = 0.001 and A", B", C", D" with a = 0.003.

In this molecule, as in silicon tetrabromide, it may be seen that the effect of changing the tem-

perature factor is quite distinct from the effect of in changing the model. This is not true in general; for example, in diffuorodibromosilane it is difficult

for example, in diffuorodibromosilane it is difficult to decide on a model because the application of the temperature factor produces changes in the curves that cannot be distinguished from changes brought about by varying the structural parameters slightly.

The singly primed curves show the best agreement with the photographs with respect to the effect of the temperature factor, in that the doubly primed group loses too much detail beyond s =20, and the unprimed group shows many features too sharply. This indicates that a = 0.001 is approximately correct. The singly primed curves are not shown below s = 14 because small differences in the temperature factor have virtually no effect in this region. The curve C' represents the appearance of the photographs quite adequately.

The curves D, D' and D" for $\vartheta = 107^{\circ}$ can be eliminated because they show minimum 9 deeper than 10, maximum 11 higher than 12, and minimum 6 deeper than 8. These difficulties persist for all values of a.

The curves A, for $\vartheta = 113^{\circ}$, are unsatisfactory because they show minima 6 and 7 with the same

depth, maximum 6 too low compared with 7, maxima 8 and 9 too nearly equal, and minimum 12 too deep compared with 11 and 13.

The curves C for $\vartheta = 109^{\circ}28'$, and B for $\vartheta = 111^{\circ}$ are almost identical. The only respect in which curves C disagree with the photographs is that they show minimum 8 slightly shallower than 6.

Table II gives $s_{obs.}/s_{calcd.}$ for models B and C. In both cases, the Br-Br distance agrees well with the radial distribution value of 3.55 Å., but the tetrahedral model gives a long value for the Si-Br distance-2.18 Å. compared with the radial distribution value of 2.16 Å. The peaks of the radial distribution curve lead to the value $110^{1/2}$ ° for ϑ . For this reason, as well as the slight qualitative superiority of C, we choose our final model closer to C than B, but assign limits of error which e best values are

$$l_{\text{Si-Br}} = 2.16 \pm 0.03 \text{ A.}$$

$$\angle \text{Br-Si-Br} = 110^{1}/_{2} \pm 1^{1}/_{2}^{\circ}$$

$$l_{\text{Br-Br}} = 3.55 \pm 0.02 \text{ Å.}$$

$$a_{\text{Br-Br}} = 0.001$$

~ . .

Difluorodibromosilane.—The photographs showed eleven measurable rings. The pattern is well represented by curve J (Fig. 3) except for peaks 3–4 and 9. The exact nature of these features is doubtful. The maximum labeled 3–4 is quite broad and appeared at first glance to be rather more flat-topped than the figure indicates. For this reason two terms, numbers 3 and 4, were put into the radial distribution function to represent the extra width. The appearance of the ninth maximum and adjacent minima was also uncertain; hence *s* values for these features were not used in the quantitative comparison.

Fourteen theoretical curves (Fig. 3) were calculated for symmetrical (C_{2v}) tetrahedral models with $l_{\text{Si-Br}} = 2.16$ Å., $l_{\text{F-Br}}$ ranging from 3.01 to 3.11 Å. and $l_{\text{Br-Br}}$ from 3.49–3.61 Å. as suggested by the radial distribution function peaks (Fig. 1c) at 2.15, 3.07 and 3.56 Å. Because the appearance of the theoretical curves is insensitive to variations in the Si-F distance, and the radial distribu-

Fig. 2.—Simplified theoretical intensity curves for SiHBr₃.



MOLECULAR STRUCTURES OF SOME SILICON POLYHALIDES

				TAE	BLE II			
Max.	Min.	I_n	C_n	50	s_{C}^{a}	SC/50	$s_{\mathbf{B}^{b}}$	sB/so
	1	- 3	- 1	1.64				
1		4	2	2.35				
	2	- 6	- 3	3.06				
2		10	7	3.97				
	3	-10	- 9	4.92				
3		6	6	5.97	5.91	(0.990)	5.93	(0.993)
	4	- 4	- 5	6.68	6.78	1.015	6.70	1.003
4		4	5	7.42	7.52	1.013	7.58	0.999
	5	- 9	-12	8.45	8.38	0.992	8.31	. 983
5		10	14	9.37	9.47	1.011	9.36	. 999
	6	- 7	- 10	10.31	10.45	1.014	10.38	1.007
6		4	6	11.18	11.33	1.013	11.18	1.000
	7	- 3	- 5	11.88	11.92	1.003	11.72	0.987
7		7	10	12.77	12.85	1.006	12.75	.998
	8	-10	-15	13.83	13.89	1.004	13.79	.997
8		10	14	14.80	14.92	1.008	14.83	1.002
	9	- 7	- 3	15.58	15.86	1.026	15.55	0.998
9		2	3	16.25	16.51	1.016	16.31	1.004
	10	-10	-13	17.24	17.31	1.004	17.15	0.995
10		10	12	18.19	18.38	1.011	18.23	1.002
	11	- 8	- 9	19.25	19.42	1.009	19.22	0.998
11		4	4	20.00	20.39	1.020	20.09	1.005
	12	- 1	- 1	20.70	21.04	1.017	20.69	1.000
12		6	5	21.43	21.84	1.019	21,63	1.009
	13	- 9	- 7	22.59	22.85	1.012	22.69	1,005
13		5	4	23,44	23.87	1.019	23.75	1.013
	14	- 1	- 1	24.05	24.89	(1.035)	24.61	(1.023)
14		6	4	24.57	25.65	(1.043)	25.08	(1.021)
	15	-10	- 6	25.55	26.21	(1.027)	25.98	(1.017)
15		7	3	27.01	27.25	(1.008)	(27.19)	(1.007)
					Average	1.012		1,000
					Av. dev.	0.006		0.005
					l_{Si-Br}	2.175		2.15
					l_{Br-Br}	3.55		3.54

^a Br-Si-Br = 109°28′. ^b Br-Si-Br = 111°.

tion function does not show a corresponding, well resolved peak, the value 1.545 Å. was assumed, in agreement with the Si–F distance found in silicon tetrafluoride.⁶ This assumption may be partially justified by analogy with CF_2Cl_2 and CF_4 ,⁷ in both of which the C–F distance is the same. It should be borne in mind that the reported values of the Br–Si–F and F–Si–F angles are also essentially assumed values inasmuch as they depend on the assumed Si–F distance.

The models investigated were systematized by locating them on a two-dimensional map of $l_{\rm F-Br}$ against $l_{\rm Br-Br}$. All models lying outside a closed curve corresponding to the assigned limits of error are inacceptable, and, in general, become progressively worse as their distance from the selected points increases in any direction. Since it was impossible, as discussed above, to determine the temperature factor experimentally, the value $a_{\rm Br-Br} = 0.001$, which is approximately equal to that obtained for the Br-Br vibration in SiBr₄ and SiHBr₃, was adopted here for both $a_{\rm Br-Br}$ and $a_{\rm Br-F}$. $a_{\rm Si-F}$, $a_{\rm F-F}$, and $a_{\rm Si-Br}$ were all arbitrarily set at zero.

The curves disagreed with the photographs as follows: (a) Curves A, B and D show minimum 7 too deep, relative to minima 6 and 8. Curve D also reverses the relative depths of minima 3 and 5, and makes maximum 3 too high compared with 5. (b) In curves K and N, minimum 5 is deeper than 6, contrary to the appearance of the photographs. K also shows the fifth maximum higher than the second. C and G are also unsatisfactory in the latter respect. (c) L and H give maximum 3 too high relative to 5, and minimum 3 deeper than 5.

None of the group E, F, I, J or M is definitely inacceptable, hence the assigned limit of error

⁽⁶⁾ L. O. Brockway, J. Phys. Chem., 41, 747 (1937).

⁽⁷⁾ L. O. Brockway and F. T. Wall, THIS JOURNAL, 56, 2372 (1934).

Fig. 3.—Simplified theoretical intensity functions for SiF_2Br_2 . The models are described by the following parameters:

	l _{Br-Br}	lpBr	$l_{\mathbf{F}-\mathbf{F}}$	∠ BrSiBr	∠ F-Si-Br	∠ FSiF
A	3.53	3.05	2.07	114°10′	113°55'	93°50'
в	3.63	3.09	2.23	114°10'	112°0'	92°25'
С	3.63	3.06	2.37	114°10'	110°20'	100°10′
D	3.59	3.12	2.13	112°10'	113°55'	87°5'
E	3.59	3.09	2.29	112°10'	112°0′	95°15'
F	3.59	3.06	2.41	112°10'	110°20'	102°40'
G	3.59	3.02	2.55	112°10'	108°10′	112°5'
н	3.55	3.12	2.19	110°10'	113°55'	90°0′
I	3.55	3.09	2.33	110°10′	112°0'	97°40′
J	3.55	3.06	2.45	110°10′	110°20'	104°50'
K	3.55	3.02	2.59	110°10'	108°10′	114°0'
L	3.51	3.09	2.37	108°30′	112°0'	99°50'
м	3.51	3.06	2.48	108°30'	110°20 ⁷	106°45'
N	3.51	3.02	2.61	108°30'	108°10'	115°30'
1	- 9.16	\$ 7	- 1 547	Å fan all made	1a	

 $s_{i-Br} = 2.16 \text{ A.}, l_{Bi-F} = 1.547 \text{ A.}$ for all models.

allows the range of parameters covered by these models. The values of $s_{calcd} \cdot s_{obs.}$, which vary little from one curve to another, are given in Table III for curve J.

Curve O, which includes only Si-Br and Si-F

interactions, shows the effect of an infinite temperature effect on the Br-Br and Br-F vibrations. The selected best values are

Previous Work.—Wouters, De Hemptinne and Capron⁸ have used the electron diffraction method to determine the structure of SiHBr₃. They obtain the results

$$l_{\text{Si-Br}} = 2.19 \pm 0.05 \text{ Å}.$$

 $l_{\text{Br-Br}} = 3.63 \text{ Å}.$
 $\angle \text{Br-Si-Br} = 110^{\circ}$

These values for the Br-Br distance and the Si-Br distance are significantly higher than ours although the bond angle values agree well. We believe the present determination to be the more reliable because Wouters and coworkers measured only the first five maxima, whereas we measured fifteen maxima and fifteen minima. It has been our experience that determinations based on a few measurements extending to only relatively small values of s are likely to be inaccurate, particularly if the minima are neglected. Moreover, it may be significant that the above authors have reported several other interatomic distances which appear to be too high by about their assigned experimental error. Their determination of the size of the SiHCl₃⁹ molecule gives a result 2 to 3% higher than that obtained by Brockway³ and by Pirenne.¹⁰ For SiBrCl₃^{9b} De Hemptinne and Wouters again re-

port 2.19 Å, for the Si-Br distance, and give 2.05 Å.



⁽⁸⁾ Wouters, De Hemptinne and Capron, Ann. soc. sci. Bruxelles, 574, 25 (1937).

^{(9) (}a) De Hemptinne and Wouters, Nature, 138, 884 (1936);
(b) 139, 928 (1937).

⁽¹⁰⁾ Pirenne, J. Chem. Phys., 7, 144 (1939).

			· TAI	BLE III			12	10	6	23.96
Max.	Min.	I_n	C_n	50	sj	sj/so				Avera
	1	- 5	- 4	1.61						Av. a
1		6	4	2.49	2.45	(0.984)	a See to	et for disauss	ion	₽Si−Br
	2	- 8	- 6	3.20	3.22	1.005	See le.	at for discuss	1011.	
2		10	9	4.21	4.18	0.993	for the \$	Si–Cl dista	nce,	a val
	3	- 7	- 8	5.14	5.28	1.027	that (2.0	01 Å.) whie	ch h	ias be
3		5	7	6.23	6.47^{a}	(0.972)	Si-Cl bo	nd in other	mo	lecule
4		5	7	7.08				nu m ounci	~	iccuic
	5	-11	-17	7.89	7.87	. 997			Sun	nmary
5		10	16	9.03	9.07	1.003	The n	iolecular st	ruct	ures o
	6	- 5	- 8	10.10	10.19	1.010	SiF ₂ Br ₂ 1	nave been s	tudi	ed by
6		3	4	10.91	10.90	0.999	tion met	hod In a	ll of	these
	7	- 7	-11	11.74	11.75	1.000	d'at an an	100.10 - 0	1 01	å
$\overline{7}$		10	16	12.78	12.75	0.998	distance	15 2.10 = 0	1.03	A., an
	8	-10	-16	13.74	13.84	1.008	are but l	ittle distort	ed f	rom tl
8		6	9	14.90	14.86	0.999	The rela	tive tempe.	ratu	re fac
	9	- 2	- 3	15.33	15.74	(1.027)	mated fo	or SiBr ₄ and	1 Sil	HBr₄ f
9		2	3	16.72	16.71	(1.000)	of the ele	otron diffra	otio	n nhoi
	10	- 6	- 8	17.12	17.27	(1.009)				n pno
10		10	12	18.18	18.13	0.997	(II) List	er and Sutton	(Ira Franti	ins. Far
	11	- 8	- 8	19.67	19.62	.997	silicon tetr	abromide is 2.	14 ±	0.02 Å.
11		8	7	21.25	21.24	1.000	with our va	lue.		
	12	-10	- 7	22.71	22.61	0.996	PASADENA	, Californi	A I	Receiv

12	10	6	23.96	23.61	(0,969)
			Average	e	1.002
		A	Av. dev	Av. dev.	
			$l_{\rm Si-Br}$		2.16
a 🔿 .		•			

lue 2% higher than en reported for the s.11

of SiBr₄, SiHBr₃ and the electron diffracmolecules the Si-Br d the valence angles he tetrahedral value. tors have been estifrom the appearance tographs.

aday Soc., 37, 393 (1941)] y that the Si-Br distance in , in substantial agreement

YED SEPTEMBER 13, 1941

[CONTRIBUTION FROM THE DEPARTMENT OF BIOLOGICAL CHEMISTRY, WASHINGTON UNIVERSITY SCHOOL OF MEDICINE. ST. LOUIS, MISSOURI]

Preparation of Tetrahydroxyquinone and Rhodizonic Acid Salts from the Product of the Oxidation of Inositol with Nitric Acid*

By PAUL W. PREISLER AND LOUIS BERGER

Some confusion exists in the literature concerning the identification of the salts of rhodizonic acid (dihydroxy-diquinone) and of tetrahydroxyquinone. The quantitative analytical procedures usually employed for this purpose do not distinguish with certainty between substances of such close elementary composition, especially when they are hydrated or cannot be properly dried.¹ These materials have now been conclusively identified by application of electrometric oxidationreduction potential measurements.

Modification of the methods for the preparation of these substances from the products of the oxidation of inositol (cyclohexanehexol) by nitric acid have been devised and crystalline materials of high purity have been prepared. The quantities of rhodizonate or of tetrahydroxyquinone salt have been found to be affected by the rate of the addition and the basic properties of the salt added to the oxidized inositol, and by the degree of agitation with air or oxygen of the mixture so formed. When potassium acetate is used, pure potassium rhodizonate is obtained, whereas with potassium carbonate mixtures with tetrahydroxyquinone, salts usually result.

Salts of rhodizonic acid and of tetrahydroxyquinone are utilized as indicators in the volumetric determination of sulfates with barium salt solution.² A comparison of the properties of the pure substances indicates that the color changes when used as indicators are probably due to salts of rhodizonic acid rather than of tetrahydroxyquinone.

Preparation of Oxidation Products of Inositol .-- To ensure uniform reproducible results the procedure is given in

^{*} Presented before the American Chemical Society at St. Louis, Mo., April, 1941.

⁽¹⁾ E. Bartow and W. W. Walker, Ind. Eng. Chem., 30, 300 (1938); O. Gelormini and N. E. Artz, This JOURNAL, 52, 2483 (1930); F. A. Hoglan and E. Bartow, *ibid.*, 62, 2397 (1940); B. Homolka, Ber., 54, 1393 (1921); M. Maquenne, Compt. rend., 104, 297 (1887); R. Nietzki and T. Benckiser, Ber., 18, 499 (1885).

⁽²⁾ G. Gutzeit, Helv. Chim. Acta, 12, 725 (1929); W. A. Peabody and R. S. Fisher, Ind. Eng. Chem., Anal. Ed., 10, 651 (1938); W. C. Schroeder, Ind. Eng. Chem., Anal. Ed., 5, 403 (1933);
 5, 127 (1936); 9, 69 (1937); 10, 206 (1938); R. Strebinger and L. Zombory, Z. anal. Chem., 79, 1 (1929).